L Number	Hits	Search Text	DB	Time stamp
1	914	(MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT;	2004/10/04 10:45
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB;	
	-	SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
		near1 OSAMU).in.	DERWENT;	
•	040	// · · · · · · · · · · · · · · · · · ·	IBM_TDB	
2	213	((MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT;	2004/10/04 10:59
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB;	
		SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
		near1 OSAMU).in.) and organic	DERWENT;	
,	00	///	IBM_TDB	,
3	30	(((MINO near1 NORIHISA).in. (KAWAWAKE near1	USPAT;	2004/10/04 10:56
		YASUHIRO).in. (MORITA near1 KIYOYUKI).in. (YOSHII near1	US-PGPUB;	
		SHIGEO).in. (MURAKAMI near1 MUTUAKI).in. (KUSUMOTO	EPO; JPO;	
		near1 OSAMU).in.) and organic) and (assemble assembly	DERWENT;	
	_	self\$1assembly self\$1assembled array)	IBM_TDB	
4	3	6730395.pn.	USPAT;	2004/10/04 10:57
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
5	13	("6730395" "20020176957" "6593000" "6521334" "6503567"	USPAT;	2004/10/04 10:59
		"6410152" "6342716" "6277444" "5871815" "5515190"	US-PGPUB	
	0.4.0.0.0	"6159620" "6232777" "6341053").pn.		
6	613089	(M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:11
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.	DERWENT;	
_			IBM_TDB	
7	378	((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:50
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
_		(ordered adj particles))	_	
8	243	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
1		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
1		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
		(ordered adj particles))) and (nano nano\$1particle\$1 particle)	_	i
9	111	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
		resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
	J	(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
10		(ordered adj particles))) and (functional adj group)	_	
10	304	(((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive	USPAT;	2004/10/04 11:31
ļ		magneto\$1resistance (magneto adj resistive) (magneto adj	US-PGPUB;	
	1	resistance) (magnetic adj (head element memory sensor	EPO; JPO;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and	DERWENT;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array)	IBM_TDB	
		(ordered adj particles))) and (polymer mono\$1mer\$1 organic)	_	

12	92	((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer mono\$1mer\$1 organic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 11:44
		resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer	EPO; JPO; DERWENT;	
		apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer	DERWENT;	
		(self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		(ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer	IBM_TDB	
		and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		(ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer		
		(ordered adj array) (ordered adj particles))) and (polymer		
			1	
	1	monos (mers) organic))		
	6189	black.in.	USPAT;	2004/10/04 11:44
40			US-PGPUB;	2004/10/04 11.44
40		•	EPO; JPO;	
40			DERWENT:	
40			IBM TDB	
13	478	black.in. and (nano nano\$1particle\$1 particle)	USPAT:	2004/10/04 11:45
		, ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	107	(black.in. and (nano nano\$1particle\$1 particle)) and magnetic	USPAT;	2004/10/04 11:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
45	2405	// 1004 1.104 / 15 P 1.104 (S)	IBM_TDB	
15	3185	((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered	USPAT;	2004/10/04 11:52
		adj array) (ordered adj particles)		
16	72	(((salf\$1assamh \$4 (salf adi assamh \$4)) adi array (a-da-a-d		2004/40/04 44:50
	'2	adi array) (ordered adi narticles)) and (organic neer)		2004/10/04 11:52
		· · · · · · · · · · · · · · · · · · ·	DERWENT;	
			IBM TDB	
16	72	adj array) (ordered adj particles) (((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered adj array) (ordered adj particles)) and (organic near4 functional)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/10/04 11:52

17 18 19	70	((((self\$1assembl\$4 (self adj assembl\$4)) adj array) (ordered adj array) (ordered adj particles)) and (organic near4 functional)) not ((("6730395" "20020176957" "6593000" "6521334" "6503567" "6410152" "6342716" "6277444" "5871815" "5515190" "6159620" "6232777" "6341053").pn.) ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (nano nano\$1particle\$1 particle)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (functional adj group)) and ((((M\$1R G\$1M\$1R T\$1M\$1R T\$1M\$1R T\$1M\$1J magneto\$1resistive magneto\$1resistance (magneto adj resistive) (magneto adj resistance) (magnetic adj (head element memory sensor apparatus)) spin\$1valve\$1 (spin adj valve)).ti,ab,clm.) and (self\$1assembl\$4 (self adj assembl\$4) (ordered adj array) (ordered adj particles))) and (polymer mono\$1mer\$1 organic))) ((black.in. and (nano nano\$1particle\$1 particle)) and magnetic)) ("6162532" "20020022111" "6730395" "6420086" "4618509" "5670257" "6103868").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 12:01 2004/10/04 12:02 2004/10/04 12:02
	19	"6410152" "6342716" "6277444" "5871815" "5515190" "6159620" "6232777" "6341053").pn.) (("6162532"	USPAT; US-PGPUB	2004/10/04 12:02
		"20020022111" "6730395" "6420086" "4618509" "5670257" "6103868").pn.)		